

Amendments to the Specification:

Please replace the paragraph beginning at page 8, line 11, with the following amended paragraph:

An interlayer dielectric layer 110 is formed out of silicon oxide or a resinous material such as ~~silicon oxide~~ or polyimide to a thickness of 6000 Å. Where a silicon oxide film is formed, a liquid which is applied when the silicon oxide film is formed may be used. Finally, contact holes are formed, and pixel electrodes 111 are fabricated from ITO. In this way, thin-film transistors arranged at the pixel electrodes of the active matrix liquid crystal display can be fabricated, using the transparent resinous substrate (Fig. 1(E)).